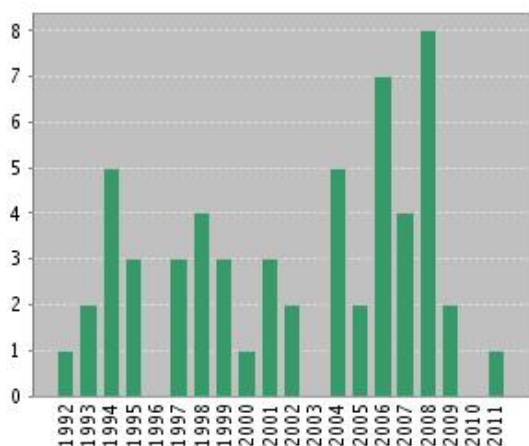


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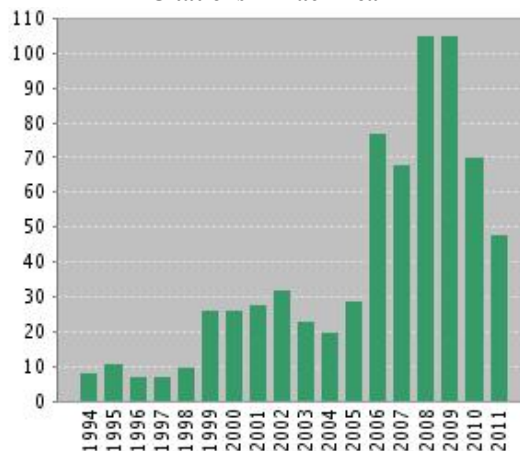
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1. **Title:** Bias-induced threshold voltages shifts in thin-film organic transistors

Author(s): Gomes HL; Stallinga P; Dinelli F; et al.

Source: APPLIED PHYSICS LETTERS **Volume:** 84 **Issue:** 16 **Pages:** 3184-3186 **DOI:** 10.1063/1.1713035 **Published:** APR 19 2004

20 17 15 8 5 93 11.62

2. **Title:** Tetracene-based organic light-emitting transistors: optoelectronic properties and electron injection mechanism

Author(s): Santato C; Capelli R; Loi MA; et al.

Conference: Symposium on Organic Field-Effect Transistors - Towards Molecular Scale held at the 2004 Annual E-MRS Spring Meeting **Location:** Strasbourg, FRANCE **Date:** MAY 24-28, 2004

Sponsor(s): European Mat Res Soc

Source: SYNTHETIC METALS **Volume:** 146 **Issue:** 3 **Pages:** 329-334 **DOI:** 10.1016/j.synthmet.2004.08.028 **Published:** NOV 3 2004

10 10 6 3 3 56 7.00

3. **Title:** Space-separated quantum cutting with silicon nanocrystals for photovoltaic applications

0 9 23 14 9 55 13.75

	2007	2008	2009	2010	2011	Total	Average Citations per Year
	68	105	105	70	48	700	38.89
<p>Author(s): Timmerman D.; Izeddin I.; Stallinga P.; et al. Source: NATURE PHOTONICS Volume: 2 Issue: 2 Pages: 105-109 DOI: 10.1038/nphoton.2007.279 Published: FEB 2008</p>							
4.	<p>Title: Identification of the silicon vacancy containing a single hydrogen atom by EPR Author(s): Nielsen BB; Johannesen P; Stallinga P; et al. Source: PHYSICAL REVIEW LETTERS Volume: 79 Issue: 8 Pages: 1507-1510 DOI: 10.1103/PhysRevLett.79.1507 Published: AUG 25 1997</p>						
	1	0	4	1	1	51	3.40
5.	<p>Title: Electron paramagnetic resonance study of hydrogen-vacancy defects in crystalline silicon Author(s): Stallinga P; Johannesen P; Herstrom S; et al. Source: PHYSICAL REVIEW B Volume: 58 Issue: 7 Pages: 3842-3852 DOI: 10.1103/PhysRevB.58.3842 Published: AUG 15 1998</p>						
	0	0	3	1	0	47	3.36
6.	<p>Title: Electronic transport in field-effect transistors of sexithiophene Author(s): Stallinga P; Gomes HL; Biscarini F; et al. Source: JOURNAL OF APPLIED PHYSICS Volume: 96 Issue: 9 Pages: 5277-5283 DOI: 10.1063/1.1789279 Published: NOV 1 2004</p>						
	8	7	5	5	1	40	5.00
7.	<p>Title: Analysis of deep levels in a phenylenevinylene polymer by transient capacitance methods Author(s): Gomes HL; Stallinga P; Rost H; et al. Source: APPLIED PHYSICS LETTERS Volume: 74 Issue: 8 Pages: 1144-1146 DOI: 10.1063/1.123469 Published: FEB 22 1999</p>						
	1	5	2	1	2	37	2.92
8.	<p>Title: ELECTRON-PARAMAGNETIC-RESONANCE OF MOLECULAR-HYDROGEN IN SILICON Author(s): STALLINGA P; GREGORKIEWICZ T; AMMERLAAN CAJ; et al. Source: PHYSICAL REVIEW LETTERS Volume: 71 Issue: 1 Pages: 117-120 DOI: 10.1103/PhysRevLett.71.117 Published: JUL 5 1993</p>						
	0	0	0	0	0	33	1.74
9.	<p>Title: Electrical instabilities in organic semiconductors caused by trapped supercooled water Author(s): Gomes HL; Stallinga P; Colle M; et al. Source: APPLIED PHYSICS LETTERS Volume: 88 Issue: 8 Article Number: 082101 DOI: 10.1063/1.2178410 Published: FEB 20 2006</p>						
	4	6	10	4	4	33	5.50
10.	<p>Title: Electrical characterization of organic based transistors: stability issues Author(s): Gomes HL; Stallinga P; Dinelli F; et al. Conference: 7th International Symposium on Polymers for</p>						
	5	3	4	5	1	26	3.71

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68	105	105	70	48	700	38.89

Advanced Technologies **Location:** Ft Lauderdale, FL **Date:** SEP 21-24, 2003

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